

SANYO**FC143**

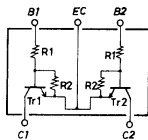
NPN Epitaxial Planar Silicon Composite Transistor
Switching Applications
 (with Bias Resistance)

Applications

- Switching circuits, inverter circuits, interface circuits, driver circuits.

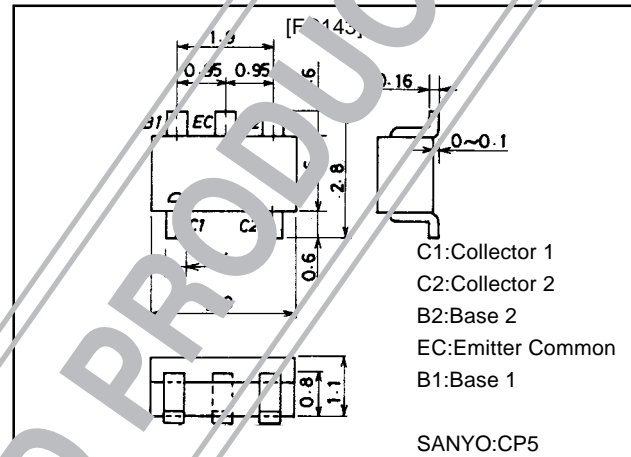
Features

- On-chip bias resistance (R1=4.7kΩ, R2=10kΩ).
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC143 is formed with two chips, being equivalent to the 2SC4360, placed in one package.
- Excellent in thermal equilibrium and pair capability.

Electrical Connection**Package Dimensions**

unit:mm

2066

**Specifications****Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		50	V
Collector-to-Emitter Voltage	V _{CE0}		50	V
Emitter-to-Base Voltage	V _{EB0}		6	V
Collector Current	I _C		100	mA
Peak Collector Current	I _{CP}		200	mA
Collector Dissipation	P _C	1 unit	200	mW
Total Dissipation	P _T		300	mW
Junction Temperature			150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CB0}	V _{CB} =40V, I _E =0			0.1	μA
Collector Cutoff Current	I _{CE0}	V _{CE} =40V, I _E =0			0.5	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0	262	340	485	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10mA	50			
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =5mA		250		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		3.3		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA		0.1	0.3	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	50			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =100μA, R _{BE} =∞	50			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} =5V, I _C =100μA	0.7	0.85	0.95	V
Input ON-State Voltage	V _{I(on)}	V _{CE} =0.2V, I _C =10mA	0.95	1.3	2.0	V
Input Resistance	R ₁		3.3	4.7	6.1	kΩ
Resistance Ratio	R _{1/R2}			0.47		

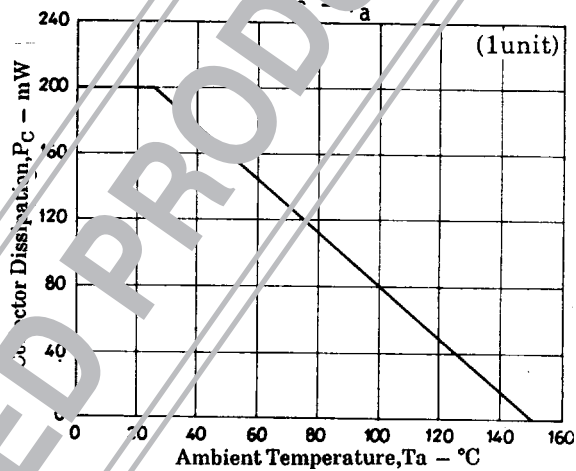
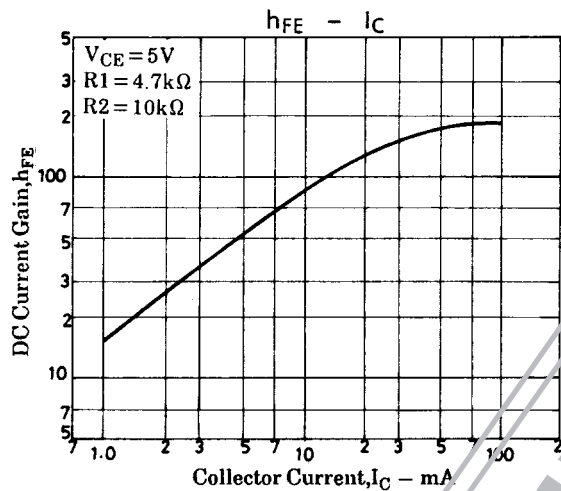
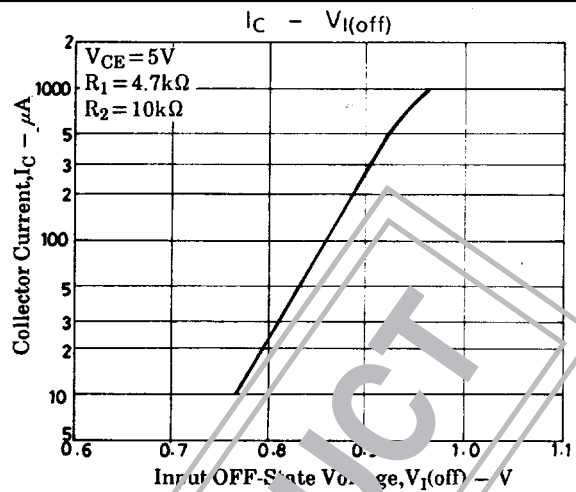
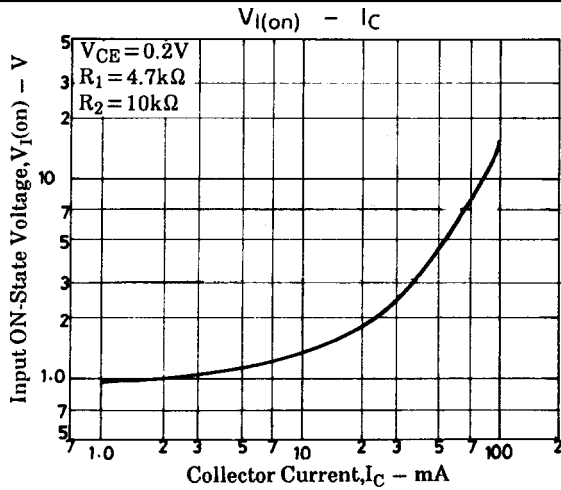
Note: The specifications shown above are for each individual transistor.

Marking:143

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FC143



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